



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

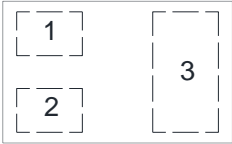
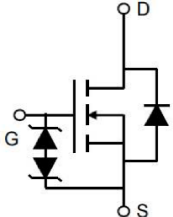
Features

- 20V, $R_{DS(ON)}=180m\Omega$ (Typ.) @ $V_{GS}=4.5V$
- $R_{DS(ON)}=260m\Omega$ (Typ.) @ $V_{GS}=2.5V$
- $R_{DS(ON)}=415m\Omega$ (Typ.) @ $V_{GS}=1.8V$
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	0.7	A
	$T_A=75^\circ\text{C}$		0.54	
Maximum Power Dissipation		P_D	0.22	W
Pulsed Drain Current		I_{DM}	2.8	A
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Lead Temperature		T_L	260	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10\text{s}$	$R_{\theta JA}$		556	$^\circ\text{C/W}$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.35	0.75	1.1	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.6A$		180	300	m Ω
		$V_{GS}=2.5V, I_D=0.5A$		260	350	
		$V_{GS}=1.8V, I_D=0.2A$		415	700	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz,$ $V_{DS}=10V$		56		pF
Output Capacitance	C_{OSS}			20		
Reverse Transfer Capacitance	C_{RSS}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A$		1		nC
Gate-to-Source Charge	Q_{GS}			0.28		
Gate-to-Drain Charge	Q_{GD}			0.22		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A, R_G=3\Omega$		2		ns
Rise Time	t_r			18.8		
Turn-Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			25		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.7A$			1.2	V

Typical Characteristic

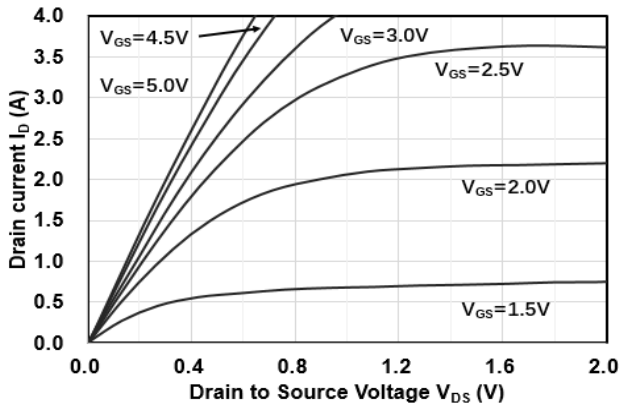


Figure1. Output Characteristics

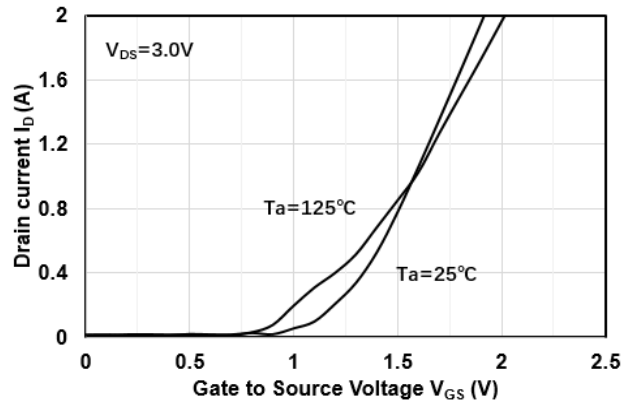


Figure2. Transfer Characteristics

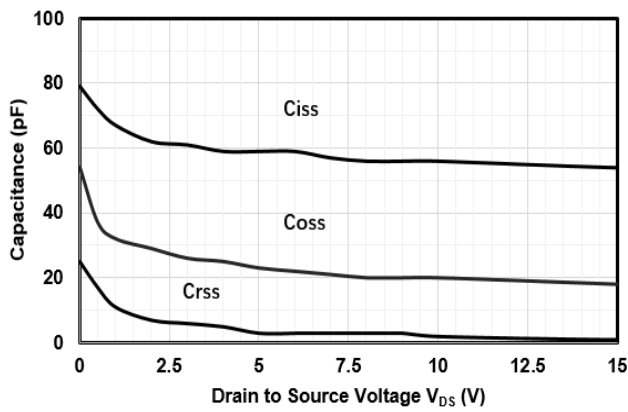


Figure3. Capacitance Characteristics

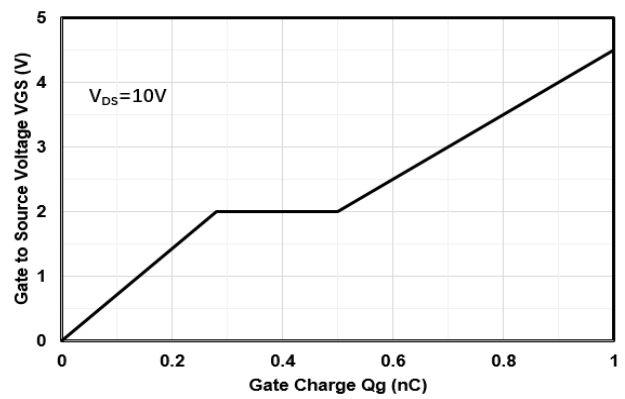


Figure4. Gate Charge

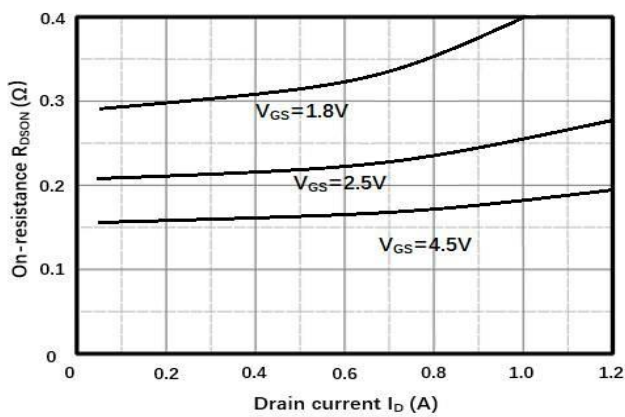


Figure5. Drain-Source on Resistance

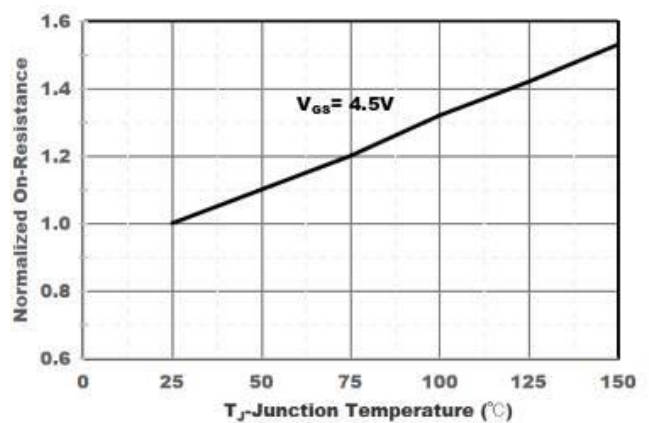


Figure6. Drain-Source on Resistance

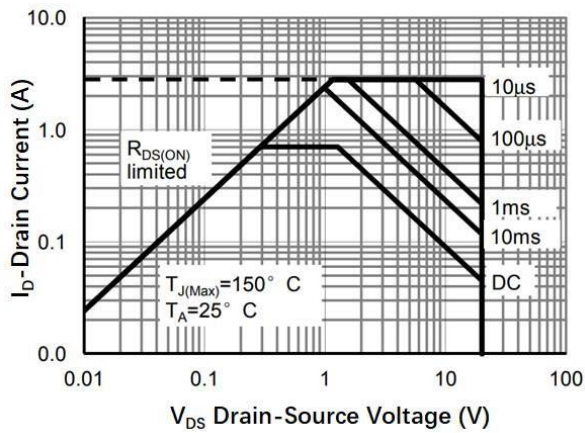


Figure7. Safe Operation Area

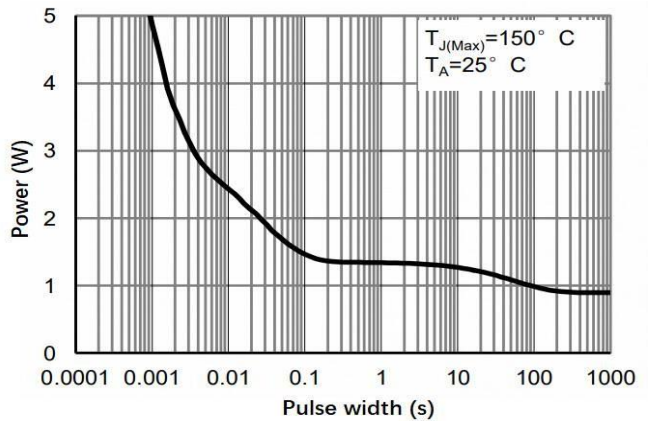


Figure8. Pulse Power Rating Junction-to Ambient

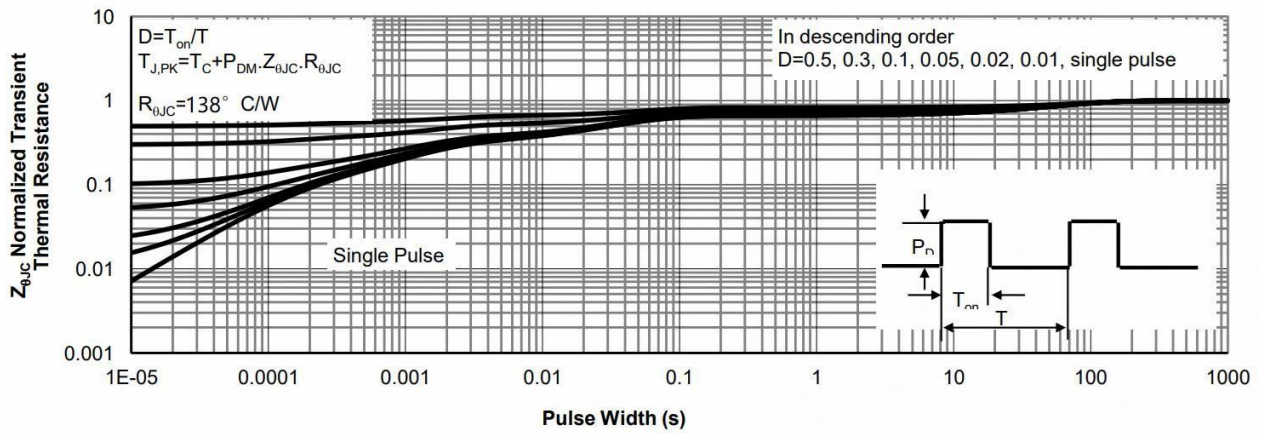
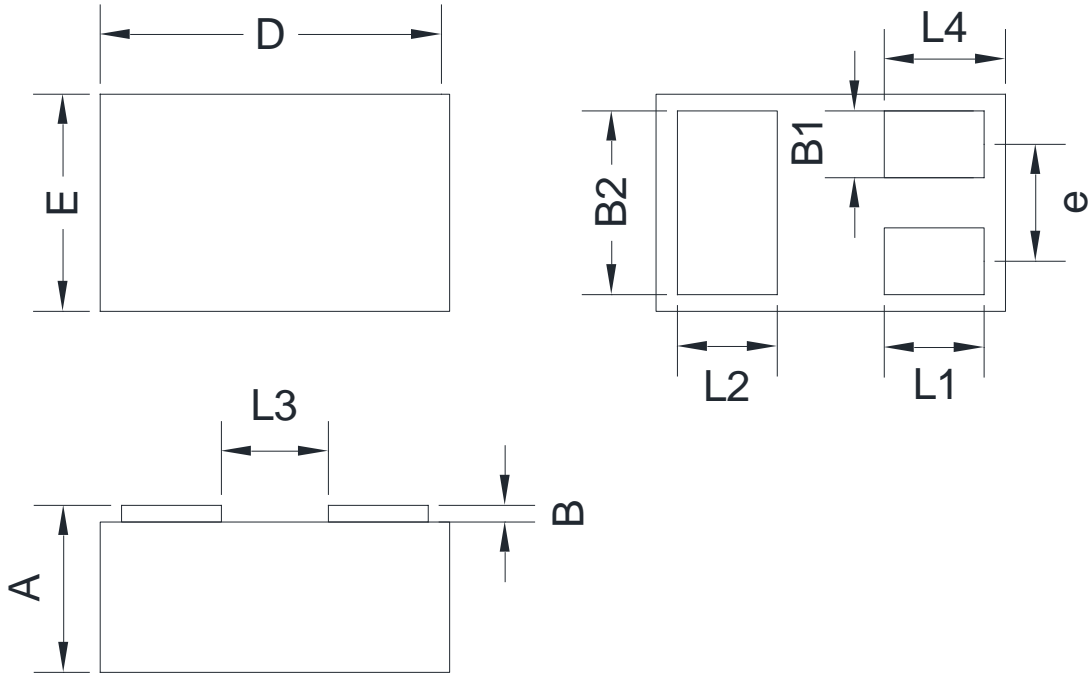


Figure9. Normalized Maximum Transient Thermal Impedance

Dimension (DFN1006-3L)


Symbol	Millimeters		Symbol	Millimeters	
	Min	Max		Min	Max
A	0.40	0.50	e	0.35	
B	0.00	0.05	L1	0.20	0.30
B1	0.10	0.20	L2	0.20	0.30
B2	0.45	0.55	L3	0.39	
D	0.90	1.05	L4	0.25	0.35
E	0.50	0.65			

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